

FORM PTO-1449 US Dept. of Commerce Patent and Trademark Office  INFORMATION DISCLOSURE STATEMENT  (use several sheets if necessary)	ATTORNEY DOCKET NO.	SERIAL NO.
	ATM-260 CIP-DIV	TBA
	APPLICANT	
	Baum et al.	
	FILING DATE	GROUP
	Herewith	1621

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ST	AA	5,840,897	11/24/1998	Kirlin et al	546	2	
	AB	5,763,633	6/9/1998	Vaartstra	556	136	
	AC	5,096,737	3/17/92	Baum et al	427	38	
	AD	5,403,620	4/4/95	Kaeszi et al	427	252	
ST	AE	5,130,172	7/14/92	Hicks et al	427	252	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLAS S	TRANSLATION YES	NO

## OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)

ST	AF	Leipoldt, et al., "Kinetics of the Substitution Reactions of $\beta$ -Diketonato-1,5-cyclo octadieneiridium(I) Complexes with Derivatives of 1, 10-Phenanthroline and 2,2'-Dipyridyl," Journal of Organometallic Chemistry, 418, (1991), pgs. 241-247.
	AG	Basson, et al., "Bromide Catalysts in the Oxidative Addition of Iodomethane to Iridium(I) Complexes," Inorganica Chimica Acta, 173 (1990), pgs. 155-158
	AH	JP 08-260148 A, (Oct 8, 1996), col. 2, lines 10-20, col. 6, lines 30-50, Figure 7 (Abstract in English)
	AI	Brouwers et al., "Photochemistry of acetylacetonato-, trifluoroacetylacetonato-, and hexafluoroacetylacetonato-dicarbonylrhodium and iridium complexes in frozen gas mixtures at 12K," J. Chem. Soc., Dalton Trans. (1982), (9), 1777-82
	AJ	Hitchcock et al., Fluorophosphine Complexes of Rhodium(I) and Iridium(I), J. Chem. Soc. Dalton Trans. (July, 1985), pgs. 1295-1301, especially page 1297
ST	AK	Gerfin et al., "Growth of Iridium Films by Metal Organic Chemical Vapor Deposition, Thin Solid Films, (April 1994), Pgs. 352-355

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP's 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

FORM PTO-1449		US Dept. of Commerce Patent and Trademark Office		ATTORNEY DOCKET NO. ATM-260 CIP		SERIAL NO. 09.453.995	
INFORMATION DISCLOSURE STATEMENT  (use several sheets if necessary)				APPLICANT Baum et al.			
				FILING DATE December 3, 1999		GROUP 1621	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
BT	AL	6,018,065	6/2000	Baum, et al.	556	136	
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLAS S	TRANSLATION YES      NO
<b>OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)</b>							
BT	AM	Advanced Inorganic Chemistry by Cotton and Wilkinson, pgs. 772					
	AN	Cho, H.J. et al., "Preparation and Characterization of Iridium Oxide Thin Films by DC Reactive Sputtering" Extended Abstracts of the 1996 International Conference on Solid State Devices and Materials, Yokohama, (1996), pgs. 721-723.					
	AO	Chen, Tung-Sheng, "Ir-Electroded BST Thin Film Capacitors for 1 Giga-bit DRAM Application", IEEE (1996) pgs 27.2.1-27.2.4					
	AP	Nakamura, Takashi et al., "Preparation of Pb(Zr,Ti)O <sub>3</sub> Thin Films on Ir and IrO <sub>2</sub> Electrodes" Jpn. J. Appl. Phys., Part 1, No. 9B, Vol. 33 (1994), pgs 5211-5214.					
BT	AQ	Chen, Tung-Sheng, "Stability of Reactive DC Sputtered Ir and IrO <sub>2</sub> Thin Films in Various Ambients", Integrated Ferroelectrics, Vol. 16 (1997), pgs 191-198.					

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